

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|---|------------------|---------|---------------------|
| L1 | 2 | ("0644380").PN. | USPAT; USOCR | OR | OFF | 2008/05/19 06:48 |
| L2 | 1 | ("6544380").PN. | USPAT; USOCR | OR | OFF | 2008/05/19 06:48 |
| L3 | 18 | ("4539068" "4585516" "4863549" "5044311" "5057185" "5110438" "5116482" "5224202" "5246881" "5272417" "5277740" "5314603" "5330606" "5332880" "5460708" "5665167" "5711816" "RE30244").PN. | USPAT | OR | OFF | 2008/05/19 06:51 |
| L4 | 44954 | (wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and ((side or sidewall or sideway or radial\$4) same (exhaust\$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 06:54 |
| L5 | 22916 | (wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and ((side or sidewall or sideway or radial\$4) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 06:55 |

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|----|-------|--|---|----|-----|---------------------|
| L6 | 10715 | ((wafer or semiconductor or substrate) same (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (plate or shower\$4) and ((side or sidewall or sideway or radial\$4) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 06:56 |
| L7 | 4823 | ((wafer or semiconductor or substrate) same (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and ((side or sidewall or sideway or radial\$4) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 06:56 |
| L8 | 1043 | ((wafer or semiconductor or substrate) same (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and (((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust \$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 06:57 |
| L9 | 18 | ("4994301").URPN. | USPAT | OR | OFF | 2008/05/19 07:16 |

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|-----|-----|--|---|----|----|---------------------|
| L10 | 792 | ((wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and (((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust \$3 or outlet or eject\$3 or discharg\$3)) and (dry\$3 or dried or supercritical) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 07:39 |
| L11 | 0 | ((wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and (((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust \$3 or outlet or eject\$3 or discharg\$3)) and (dry\$3 or dried or supercritical) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 07:42 |
| L12 | 78 | ((wafer or semiconductor or substrate) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning)) and (((hole or aperture or nozzle) with plate) or shower\$4) and (((wall near3 side) or sidewall or (vertical\$3 with wall)) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 07:43 |

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|-----|------|--|-------------------------|----|-----|------------------|
| L13 | 27 | ((wafer or semiconductor or substrate) and (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) and ((wall near3 side) or sidewall or (vertical\$3 with wall)) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 07:44 |
| L14 | 1019 | ((wafer or semiconductor or substrate) and (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 07:45 |
| L15 | 589 | ((wafer or semiconductor or substrate) with (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 07:45 |
| L16 | 565 | ((wafer or semiconductor or substrate) with (dry\$3 or dried)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4).ab. | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 07:45 |
| L17 | 0 | ("62511123").PN. | USPAT; USOCR; JPO | OR | OFF | 2008/05/19 08:45 |
| L18 | 1 | ("6251223").PN. | USPAT; USOCR; JPO | OR | OFF | 2008/05/19 08:45 |
| L19 | 1 | ("62051223").PN. | USPAT; USOCR; JPO | OR | OFF | 2008/05/19 08:46 |
| L20 | 190 | ((wafer or semiconductor or substrate) and (dry\$3 or dried or gas or gases or (supercritical))).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) and ((wall near3 side) or sidewall or (vertical\$3 with wall)) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 08:48 |

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|-----|------|---|---|----|-----|------------------|
| L21 | 4583 | ((wafer or semiconductor or substrate) and (dry\$3 or dried or gas or gases or (supercritical))).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 08:48 |
| L22 | 3001 | ((wafer or semiconductor or substrate) with (dry\$3 or dried or gas or gases or supercritical)).ab. and (((hole or aperture or nozzle) with plate) or shower\$4) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 08:49 |
| L24 | 51 | ((wall near3 side) or sidewall or (vertical\$3 with wall)) near10 (exhaust\$3 or outlet or eject\$3 or discharg\$3) and ((wafer or semiconductor or substrate) with (dry\$3 or dried or gas or gases or supercritical)) with (((hole or aperture or nozzle) with plate) or shower\$4)).ab. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 08:50 |
| L25 | 2 | ("6656838").URPN. | USPAT | OR | OFF | 2008/05/19 08:54 |
| L26 | 7 | ("5863598" "6090210" "6100149" "6287635" "6403479").FN. OR ("6656838").URPN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/05/19 08:54 |
| S31 | 587 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical) with ((carbon near2 dioxide) or (CO2)) with pressure) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/14 13:55 |

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|-----|-------|---|---|----|----|------------------|
| | | turn or turning) | | | | |
| S32 | 4484 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical or pressure) with ((carbon near2 dioxide) or (CO2))) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/14 13:56 |
| S33 | 2821 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical or pressure) with ((carbon near2 dioxide) or (CO2))) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/14 13:56 |
| S34 | 22976 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical or pressure) with ((carbon near2 dioxide) or (CO2) or fluid)) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/14 13:57 |

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|-----|------|--|---|----|----|---------------------|
| S35 | 1326 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and ((supercritical or subcritical) with ((carbon near2 dioxide) or (CO2))) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/14 13:58 |
| S36 | 147 | ("0002001" "0002002" "0002002" "0002003" "0002003" "0002004" "0002004" "20010013355" "20010013355" "20010017146" "20010027797" "20010047810" "20020011257" "20020025760" "20020043893" "20020086620" "20020086622" "20020088478" "20020108631" "20020115024" "20020115025" "20020139390" "20020144708" "20020153806" "20020157685" "20020157686" "20020173156" "20020173166" "20020195133" "20030024547" "20030028287" "20030061675" "20030062071" "20030064586" "20030088995" "20030106566" "20030106572" "20030106846" "20030111092" | US-PGPUB; USPAT | OR | ON | 2008/05/14 14:06 |

"20030116174" |
"20030116176" |
"20030116491" |
"20030133851" |
"20030134518" |
"20030136334" |
"20030136422" |
"20030136429" |
"20030139057" |
"20030141784" |
"20030183246" |
"20030192571" |
"20030196679" |
"20030200986" |
"20030205240" |
"20030205559" |
"20030234029" |
"20040007257" |
"20040009740" |
"20040016442" |
"20040020512" |
"20040020781" |
"20040020898" |
"20040025911" |
"20040053503" |
"20040055621" |
"20040061199" |
"20040062874" |
"20040067639" |
"20040069319" |
"20040072448" |
"20040074521" |
"20040077172" |
"20040084318" |
"20040103919" |
"20040149308" |
"20040152319" |
"20040168706" |
"20040178476" |
"3973152" | "3983515"
"4326553" |
"4336719" | "4373401"
"4602184" |
"4836684" | "4979994"
"5013366" |
"5037481" | "5090432"
"5148823" |
"5203798" | "5279316"
"5337446" |
"5379785" | "5379785"
"5462604" |
"5497662" | "5560362"
"5625249" |
"5734588" | "5865894"
"5894092" |

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|-----|------|--|-------------------------|----|----|------------------|
| | | "5927308" "5927308" "5931173" "5932044" "5932077" "6016821" "6021789" "6026832" "6039059" "6041799" "6041938" "6098643" "6119367" "6136724" "6138694" "6138698" "6140744" "6148833" "6153533" "6209555" "6220259" "6241162" "6269511" "6273100" "6276370" "6276370" "6295999" "6314974" "6343609" "6385805" "6385809" "6395096" "6398937" "6412499" "6460551" "6460551" "6463938" "6513365" "6523557" "6523557" "6539952" "6554003" "6554003" "6554688" "6582525" "6585898" "6591845" "6595224" "6599402" "6619301" "6619305" "6745494" "6880560" "6904637" "7004016").PN. | | | | |
| S37 | 6704 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower or nozzle) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/16 13:18 |

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|-----|------|--|-------------------------|----|----|------------------|
| S38 | 6719 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4 or nozzle) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/16 13:18 |
| S39 | 3678 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/16 13:19 |
| S40 | 951 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and (side or sidewall or sideway or radial\$4) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/16 13:21 |
| S41 | 131 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (high with pressure) and (plate or shower\$4) and (side or sidewall or sideway or radial\$4) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/18 23:52 |
| S42 | 0 | "200807296" | JPO | OR | ON | 2008/05/19 00:59 |

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|-----|------|---|-------------------------|----|-----|---------------------|
| S43 | 0 | ("200087296").PN. | JPO | OR | OFF | 2008/05/19 00:59 |
| S44 | 1 | ("200087296").PN. | JPO | OR | OFF | 2008/05/19 00:59 |
| S45 | 11 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (high with pressure) and (plate or shower\$4) and (sidewall) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:01 |
| S46 | 653 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and (sidewall) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:02 |
| S47 | 11 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and (sidewall with (discharge or outlet)) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:03 |
| S48 | 84 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (sidewall with (discharge or outlet)) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:04 |
| S49 | 1398 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (sidewall with (discharge or outlet)) | US-PGPUB; USPAT; USOCR | OR | ON | 2008/05/19 01:07 |

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|-----|-----|---|---|----|----|------------------|
| S50 | 439 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (sidewall near3 (discharge or outlet)) | US-PGPUB; USPAT; USOCR | OR | ON | 2008/05/19 01:08 |
| S51 | 282 | ((wafer or semiconductor or substrate) with (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing)) and (sidewall near3 (discharge or outlet)) | US-PGPUB; USPAT; USOCR | OR | ON | 2008/05/19 01:08 |
| S52 | 34 | ((wafer or semiconductor or substrate) with (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing)) and (sidewall near3 (discharge or outlet)). ab. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:10 |
| S53 | 653 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and (sidewall) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:16 |
| S54 | 309 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:19 |

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|-----|----|--|-------------------------|----|----|------------------|
| S55 | 1 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) and (high near2 pressure) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:19 |
| S56 | 12 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (plate or shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) and (supercritical or dioxide) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:20 |
| S57 | 2 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) | FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:21 |

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|-----|-------|--|---|----|----|------------------|
| S58 | 1011 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (shower\$4) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:21 |
| S59 | 24224 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((sidewall or (side near2 wall)) with (opening or aperture or outlet or hole or discharg\$4)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:22 |
| S60 | 704 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((shower\$4 or plate) with (turbulence or turbulent)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:40 |

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|-----|-----|---|---|----|-----|---------------------|
| S61 | 653 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((shower\$4 or plate) with (turbulence or turbulent)) and (side or sidewall or sideway or radial\$4) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:41 |
| S62 | 34 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (shower\$4 with (turbulence or turbulent)) and (side or sidewall or sideway or radial\$4) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:42 |
| S63 | 1 | ("6723224").URPN. | USPAT | OR | OFF | 2008/05/19 01:46 |
| S64 | 653 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and (side or sidewall or sideway or radial\$4) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:48 |

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|-----|-----|---|---|----|----|---------------------|
| S65 | 130 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and ((side or sidewall or sideways or radial\$4) with (eject \$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:48 |
| S66 | 204 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and ((side or sidewall or sideways or radial\$4) with (eject \$3 or discharg\$3 or outlet)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:48 |
| S67 | 103 | (wafer or semiconductor or substrate) and (clean \$3 or processing or dry \$3 or dried or development or etching or rinsing) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) with (turbulence or turbulent)) and ((side or sidewall or sideways or radial\$4) with (eject \$3 or discharg\$3 or outlet)) and ((high with pressure) or | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 01:49 |

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|-----|-------|--|---|----|-----|---------------------|
| | | supercritical) | | | | |
| S68 | 32 | ("4960488" "5595606" "5628829" "5665640" "5755886" "5846332" "5882411" "5906683").FN. OR ("6106625").URPN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/05/19 01:54 |
| S69 | 20013 | (wafer or semiconductor or substrate) and (dry\$3 or dried) and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) or (turbulence or turbulent or laminar)) and ((side or sidewall or sideway or radial\$4) same (exhaust\$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 02:13 |
| S70 | 694 | ((wafer or semiconductor or substrate) and (dry\$3 or dried)).ab. and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and ((plate or shower\$4) or (turbulence or turbulent or laminar)) and ((side or sidewall or sideway or radial\$4) same (exhaust\$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 02:14 |

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|-----|-----|--|---|----|-----|---------------------|
| S71 | 637 | ((wafer or semiconductor or substrate) and (dry\$3 or dried)).ab. and (rotate or rotat\$4 or rotational or spin or spinning or revolve or revolving or turn or turning) and (plate or shower\$4) and ((side or sidewall or sideway or radial\$4) same (exhaust\$3 or outlet or eject\$3 or discharg\$3)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 02:14 |
| S72 | 6 | hitachi.as. and plate and dried and (spin adj chuck) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 02:23 |
| S73 | 0 | ("4271882").PN. | JPO | OR | OFF | 2008/05/19 02:33 |
| S74 | 0 | ("40271882").PN. | JPO | OR | OFF | 2008/05/19 02:33 |
| S75 | 897 | hitachi.as. and amada. in. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 02:39 |
| S76 | 152 | hitachi.as. and amada. in. and (wafer or substrate or semiconductor) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT | OR | ON | 2008/05/19 02:39 |

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